



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Features

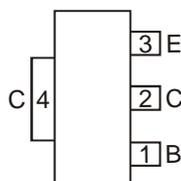
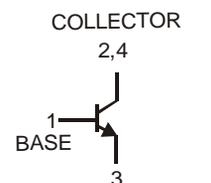
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (NK-DXTA92)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish — Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 54.8mg (approximate)



Top View


 TOP VIEW
 Device Schematic


Pin Out Configuration

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	6	V
Continuous Collector Current	I_C	500	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$	P_D	1	W
Thermal Resistance, Junction to Ambient (Note 3)	$R_{\theta JA}$	125	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	300	—	—	V	$I_C = 100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	300	—	—	V	$I_C = 1\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 100\mu\text{A}, I_C = 0$
Collector Cut-off Current	I_{CBO}	—	—	0.1	μA	$V_{CB} = 200\text{V}, I_E = 0$
Emitter Cut-off Current	I_{EBO}	—	—	0.1	μA	$V_{EB} = 6\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	0.5	V	$I_C = 20\text{mA}, I_B = 2\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	—	0.9	V	$I_C = 20\text{mA}, I_B = 2\text{mA}$
Static Forward Current Transfer Ratio	h_{FE}	25	—	—	—	$I_C = 1\text{mA}, V_{CE} = 10\text{V}$
		40				$I_C = 10\text{mA}, V_{CE} = 10\text{V}$
		40				$I_C = 30\text{mA}, V_{CE} = 10\text{V}$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f_T	50	—	—	MHz	$I_C = 10\text{mA}, V_{CE} = 20\text{V}, f = 100\text{MHz}$
Output Capacitance	C_{obo}	—	—	3	pF	$V_{CB} = 20\text{V}, f = 1\text{MHz}$

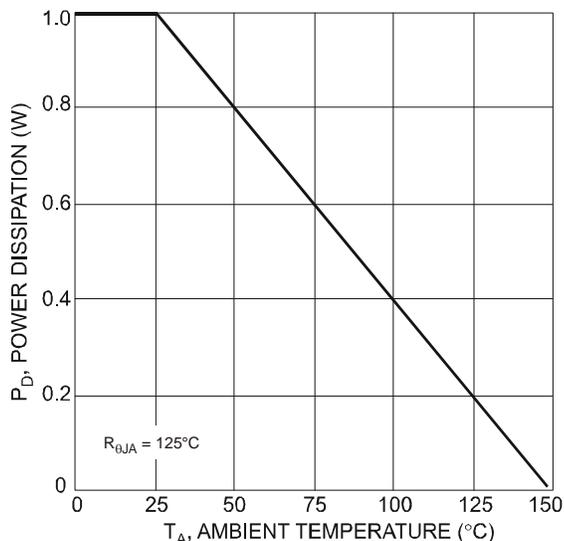


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

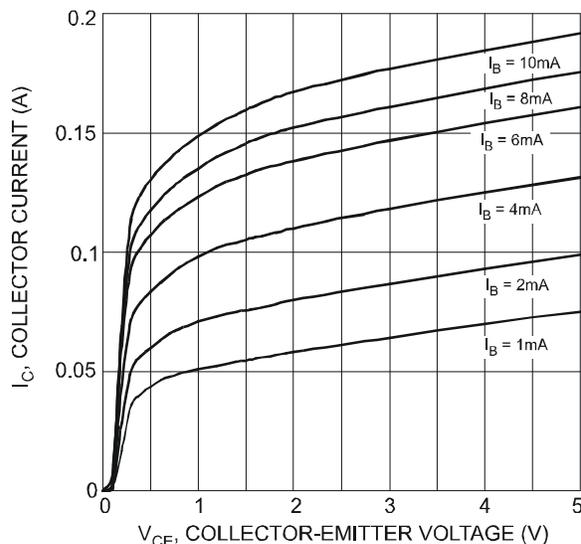


Fig. 2 Collector Current vs. Collector-Emitter Voltage

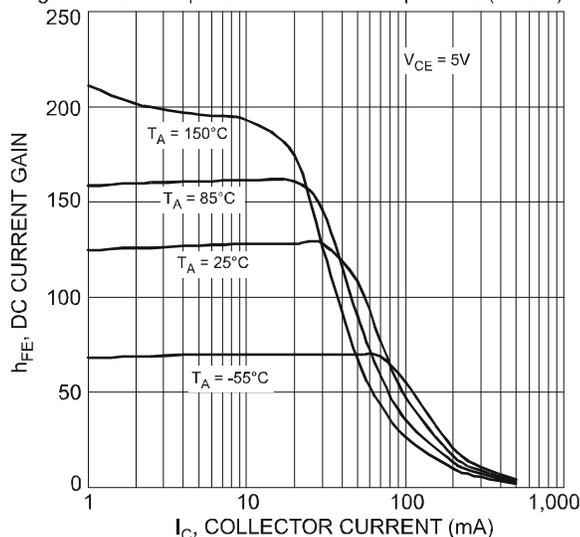


Fig. 3 Typical DC Current Gain vs. Collector Current

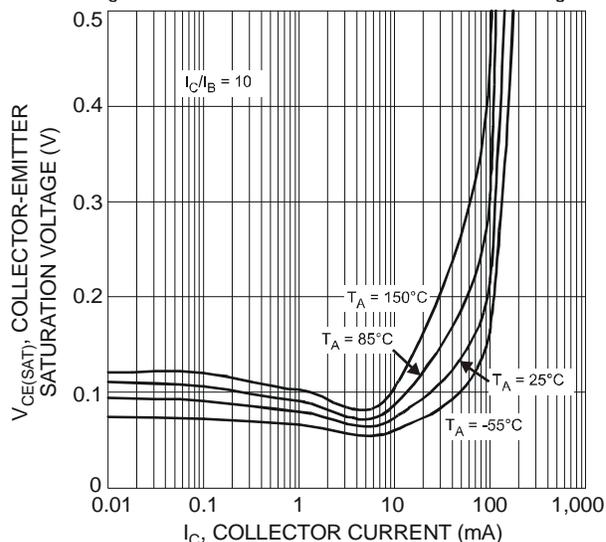


Fig. 4 Collector-Emitter Saturation Voltage vs. Collector Current

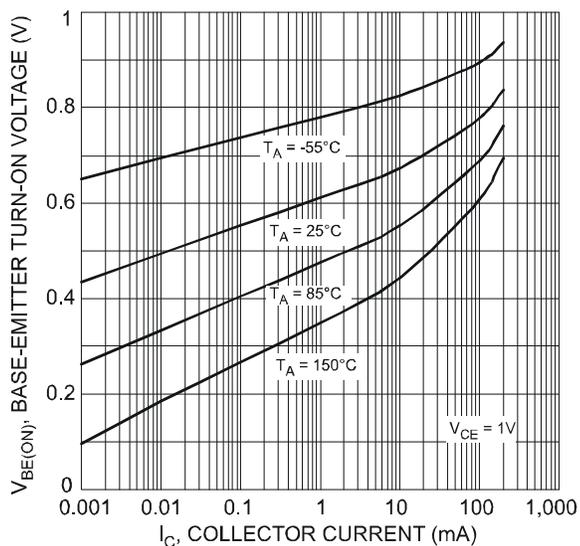


Fig. 5 Base-Emitter Turn-On Voltage vs. Collector Current

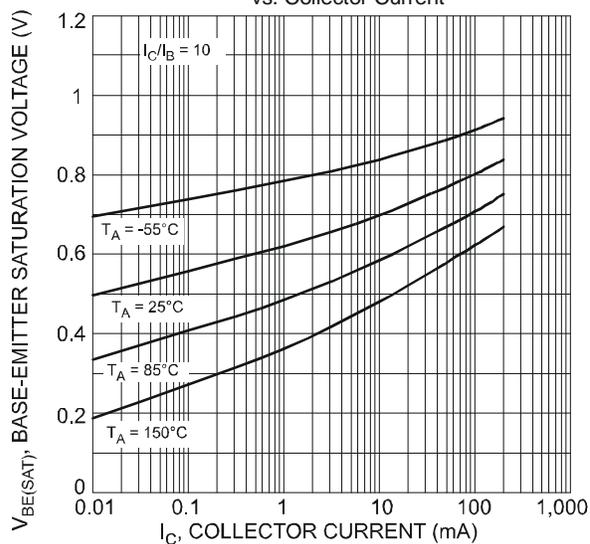


Fig. 6 Base-Emitter Saturation Voltage vs. Collector Current

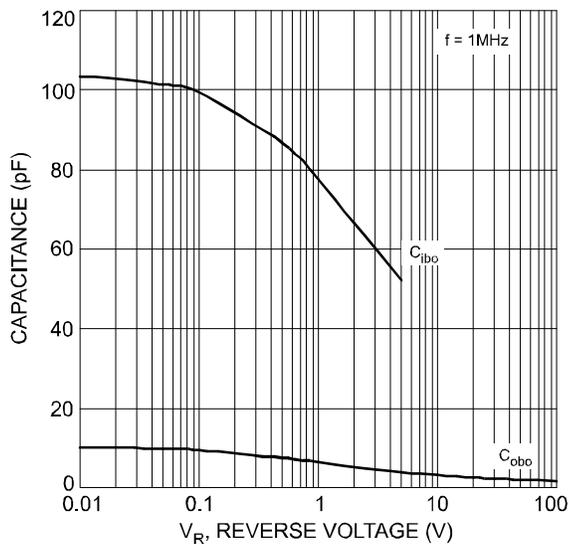


Fig. 7 Typical Capacitance Characteristics

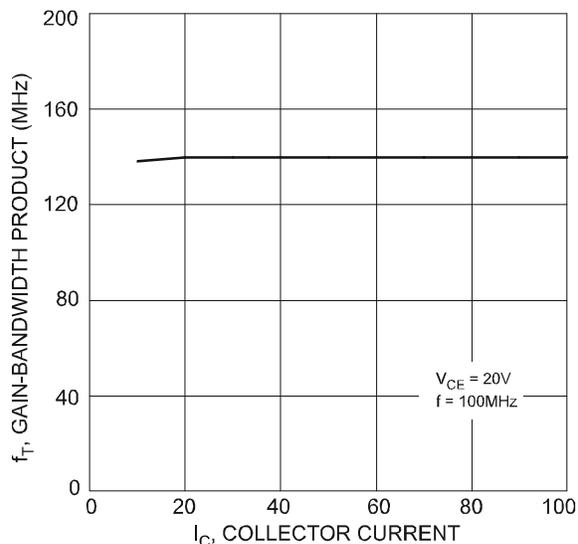
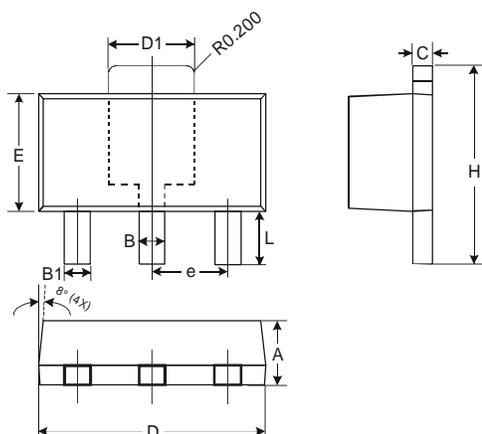


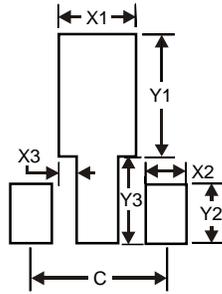
Fig. 8 Gain-Bandwidth Product vs. Collector Current

Package Outline Dimensions



SOT89-3L			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
X1	1.7
X2	0.9
X3	0.4
Y1	2.7
Y2	1.3
Y3	1.9
C	3.0